

10/577938

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of
PHILLIPS et al.

Serial No. unknown

Filed: May 3, 2006

For: STRAINED SEMICONDUCTOR DEVICES

AP20 Rec'd TCM PTO 03 MAY 2006

Atty. Ref.: 124-1158

TC/A.U.: unknown

Examiner: unknown

* * * * *

May 3, 2006

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO/SB/08a. A copy of the International Search Report, cited foreign patent documents and literature references are attached.

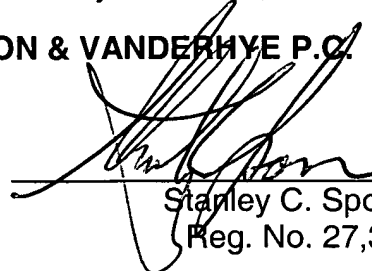
This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO/SB/08a and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted,

NIXON & VANDERHUYE P.C.

By:


Stanley C. Spooner
Reg. No. 27,393

SCS:alb
901 North Glebe Road, 11th Floor
Arlington, VA 22203-1808
Telephone: (703) 816-4000
Facsimile: (703) 816-4100

INFORMATION DISCLOSURE CITATION

ATTY. DOCKET NO.

124-1158

APPLICANT

PHILLIPS et al.

FILING DATE

May 3, 2006

SERIAL NO.

10/577938
Unknown

TC/A.U.

unknown

(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

	International Search Report of PCT/GB2004/004722, mailed 31 January 2005
	GB Search Report of GB 0326993.3, dated 23 April 2004
	LOTT et al, "STRAINED <i>p</i> -CHANNEL InGaSb/AlGaSb MODULATION-DOPED FIELD-EFFECT TRANSISTORS", Electronics Letters, Vol. 28, No. 15, 16 July 1992, Pgs. 1459-1460, XP000307703
	Patent Abstracts of Japan, JP 01 009656 A, Vol. 13, No. 184, 12 January 1989
	CUI et al., "Technology and First Electrical Characteristics of Complementary NPN and PNP InAlAs/InGaAs Heterojunction Bipolar Transistors", Japanese Journal of Applied Physics, Vol. 41, No. 28, Part 1, February 2002, Pgs. 1124-1130, XP001192196
	Patent Abstracts of Japan, JP 63 051678 A, Vol. 012, No. 268, 4 March 1988

***Examiner**

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.